

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Previously Presented) A method for forming a pattern, comprising:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed, each of the unit panels including a plurality of gate lines and data lines defining a plurality of pixels, a thin film transistor in each pixel, and a pixel electrode in each pixel;

providing a cliché on which a plurality of grooves are formed, the cliché being divided into a plurality of portions corresponding to the unit panels of the substrate;

filling resist in the grooves;

transferring the resist in the grooves of one divided portion of the cliché on a blanket applied on a surface of a printing roll by contacting and rotating the printing roll with one divided portion of the cliché, the printing roll corresponding to the respective unit panel of the substrate;

applying the resist transferred on the surface of the blanket of the printing roll on the etching object layer on a corresponding unit panel of the substrate;

transferring the resist in the grooves of other divided portion of the cliché on a blanket applied on the surface of the printing roll by contacting and rotating the printing roll with other divided portion of the cliché; and

applying the resist transferred on the surface of the blanket of the printing roll on the etching object layer on a corresponding unit panel of the substrate.

2. (Previously Presented) The method of claim 1, wherein the printing roll has a same width as that of the corresponding unit panel of the substrate.

3. (Canceled)

4. (Previously Presented) The method of claim 2, wherein a length of the blanket of the printing roll is the same as a length of a circumference of the printing roll, which is same as a length of the unit panel of the substrate.

5. (Cancelled).

6. (Cancelled).

7. (Previously Presented) The method of claim 1, wherein the printing roll is formed to have a same size as that of the unit panel the substrate.

8. (Original) The method of claim 1, wherein the etching object layer includes a metal layer.

9. (Original) The method of claim 1, wherein the etching object layer includes an insulating layer comprised of SiO_x or SiN_x.

10. (Original) The method of claim 1, wherein the etching object layer is a semiconductor layer.

11. (Previously Presented) A method for forming a pattern, comprising:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed, each of the unit panels including a plurality of gate lines and data lines defining a plurality of pixels, a thin film transistor in each pixel, and a pixel electrode in each pixel;

providing a cliché on which a plurality of grooves are formed, the cliché being divided into a plurality of areas corresponding to the unit panels of the substrate;

filling resist in the grooves of the cliché;

providing a blanket on a printing roll having a same width as that of a corresponding unit panel of the substrate;

transferring the resist filled in the grooves of one of the divided areas of the cliché onto a surface of the blanket on the printing roll by contacting and rotating the printing roll with one of the divided areas of the cliché corresponding to the unit panel of the substrate; and

applying the resist transferred on the surface of the blanket on the etching object layer on the unit panel of the substrate corresponding to the one of the divided area of the cliché;

transferring the resist filled in the groove of another of the divided areas of the cliché onto the surface of the blanket on the printing roll by contacting and rotating

the printing roll with the another of the divided areas of the cliché corresponding to another of the unit panels of the substrate; and

applying the resist transferred on the surface of the blanket on the etching object layer on the unit panel of the substrate corresponding to the another of the divided areas of the cliché.

12. (Previously Presented) The method of claim 11, wherein applying the resist on the etching object layer is performed by contacting the resist transferred on the surface of the blanket on the printing roll on the substrate and by rotating the printing roll with the blanket.

13. (Cancelled).

14. (Original) The method of claim 11, wherein the etching object layer includes a metal layer.

15. (Original) The method of claim 11, wherein the etching object layer comprises an insulating layer comprised of SiO_x or SiN_x.

16. (Original) The method of claim 11, wherein the etching object layer is a semiconductor layer.

17-27. (Cancelled)

28. (Previously Presented) The method of claim 1, wherein the blanket improves adhesive force with the resist.

29. (Previously Presented) The method of claim 11, wherein the blanket improves adhesive force with the resist.

30-34. (Cancelled)